

74LV574

Octal D-type flip-flop; positive edge-trigger; 3-state

Rev. 04 — 14 May 2009

Product data sheet

1. General description

The 74LV574 is an octal D-type flip-flop featuring separate D-type inputs for each flip-flop and non-inverting 3-state outputs for bus oriented applications. A clock (CP) and an output enable ($\overline{OE}$) input are common to all flip-flops. It is a low-voltage Si-gate CMOS device and is pin and functionally compatible with the 74HC574 and 74HCT574.

The eight flip-flops will store the state of their individual D-inputs that meet the set-up and hold times requirements on the LOW to HIGH CP transition.

When $\overline{OE}$ is LOW, the contents of the eight flip-flops is available at the outputs. When $\overline{OE}$ is HIGH, the outputs go to the high-impedance OFF-state. Operation of the $\overline{OE}$ input does not affect the state of the flip-flops.

2. Features

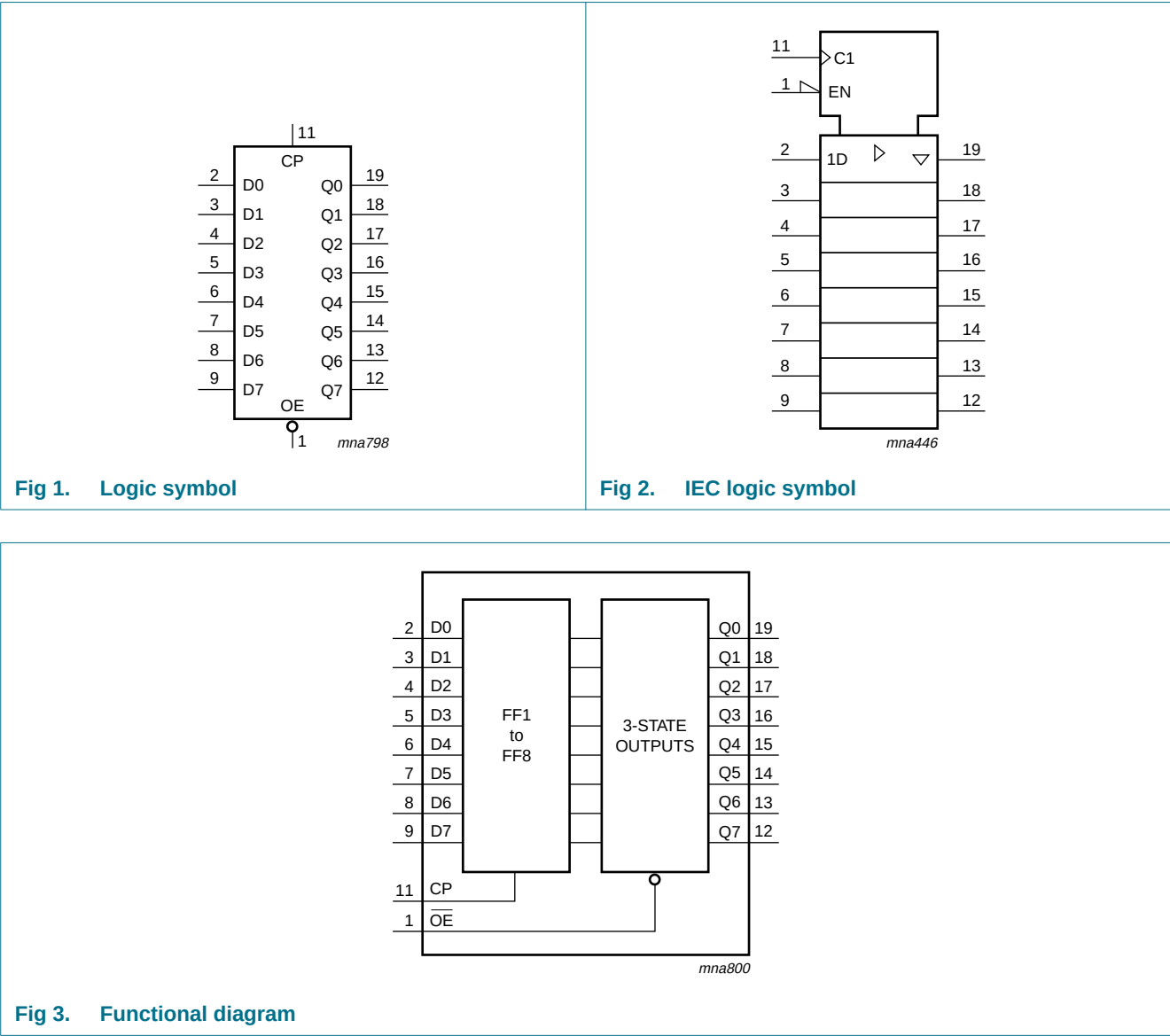
- Wide operating voltage: 1.0 V to 5.5 V
- Optimized for low voltage applications: 1.0 V to 3.6 V
- Accepts TTL input levels between $V_{CC} = 2.7$ V and $V_{CC} = 3.6$ V
- Typical output ground bounce < 0.8 V at $V_{CC} = 3.3$ V and $T_{amb} = 25$ °C
- Typical HIGH-level output voltage (V_{OH}) undershoot: > 2 V at $V_{CC} = 3.3$ V and $T_{amb} = 25$ °C
- ESD protection:
 - ◆ HBM JESD22-A114E exceeds 2000 V
 - ◆ MM JESD22-A115-A exceeds 200 V
- Common 3-state output enable input
- Multiple package options
- Specified from -40 °C to +85 °C and from -40 °C to +125 °C

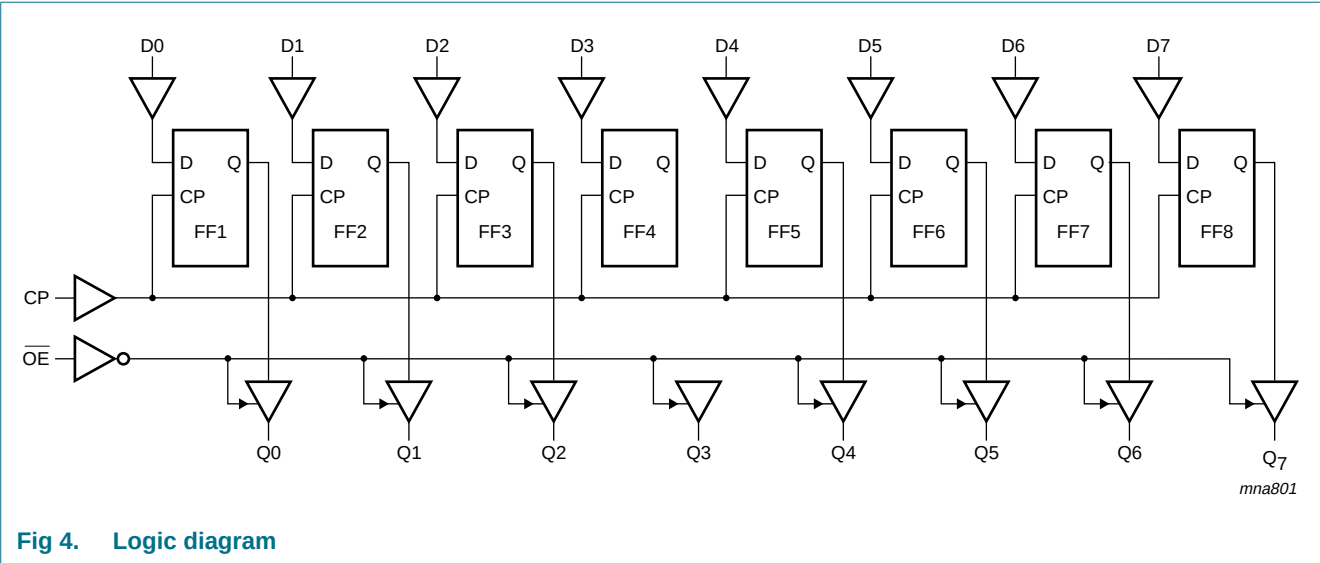
3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74LV574N	-40 °C to +125 °C	DIP20	plastic dual in-line package; 20 leads (300 mil)	SOT146-1
74LV574D	-40 °C to +125 °C	SO20	plastic small outline package; 20 leads; body width 7.5 mm	SOT163-1
74LV574DB	-40 °C to +125 °C	SSOP20	plastic shrink small outline package; 20 leads; body width 5.3 mm	SOT339-1
74LV574PW	-40 °C to +125 °C	TSSOP20	plastic thin shrink small outline package; 20 leads; body width 4.4 mm	SOT360-1

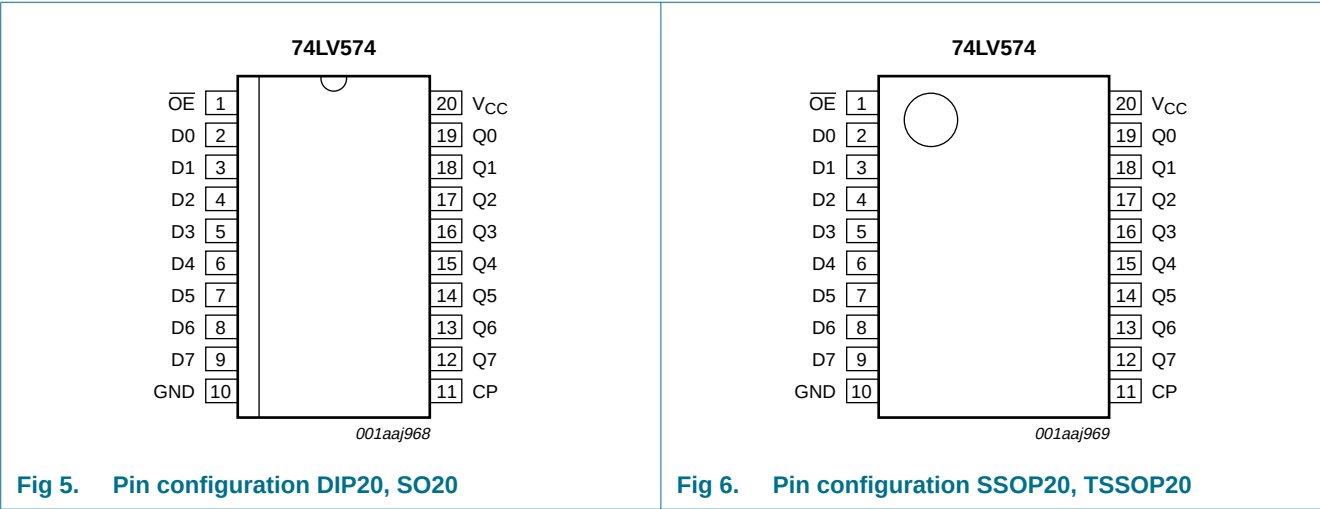
4. Functional diagram





5. Pinning information

5.1 Pinning



5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
OE	1	output enable input (active LOW)
D0 to D7	2, 3, 4, 5, 6, 7, 8, 9	data input
GND	10	ground (0 V)
CP	11	clock input (LOW to HIGH; edge triggered)
Q0 to Q7	19, 18, 17, 16, 15, 14, 13, 12	data output
V _{CC}	20	supply voltage

6. Functional description

Table 3. Function table^[1]

Operating mode	Input			Internal flip-flop	Output Qn
	OE	CP	Dn		
Load and read register	L	↑	l	L	L
	L	↑	h	H	H
Load register and disable outputs	H	↑	l	L	Z
	H	↑	h	H	Z

- [1] H = HIGH voltage level
 h = HIGH voltage level one set-up time prior to the LOW to HIGH CP transition
 L = LOW voltage level
 l = LOW voltage level one set-up time prior to the LOW to HIGH CP transition
 Z = high-impedance OFF-state
 ↑ = LOW to HIGH clock transition

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		−0.5	+7.0	V
I _{IK}	input clamping current	V _I < −0.5 V or V _I > V _{CC} + 0.5 V	^[1] -	±20	mA
I _{OK}	output clamping current	V _O < −0.5 V or V _O > V _{CC} + 0.5 V	^[1] -	±50	mA
I _O	output current	V _O = −0.5 V to (V _{CC} + 0.5 V)	-	±35	mA
I _{CC}	supply current		-	70	mA
I _{GND}	ground current		−70	-	mA
T _{stg}	storage temperature		−65	+150	°C
P _{tot}	total power dissipation	T _{amb} = −40 °C to +125 °C	^[2]		
		DIP20	-	750	mW
		SO20, SSOP20 and TSSOP20	-	500	mW

- [1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
 [2] For DIP20 packages: above 70 °C the value of P_{tot} derates linearly with 12 mW/K.
 For SO20 packages: above 70 °C the value of P_{tot} derates linearly with 8 mW/K.
 For (T)SSOP20 packages: above 60 °C the value of P_{tot} derates linearly with 5.5 mW/K.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _{CC}	supply voltage ^[1]		1.0	3.3	5.5	V
V _I	input voltage		0	-	V _{CC}	V
V _O	output voltage		0	-	V _{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	°C
Δt/ΔV	input transition rise and fall rate	V _{CC} = 1.0 V to 2.0 V	-	-	500	ns/V
		V _{CC} = 2.0 V to 2.7 V	-	-	200	ns/V
		V _{CC} = 2.7 V to 3.6 V	-	-	100	ns/V
		V _{CC} = 3.6 V to 5.5 V	-	-	50	ns/V

[1] The static characteristics are guaranteed from V_{CC} = 1.2 V to V_{CC} = 5.5 V, but LV devices are guaranteed to function down to V_{CC} = 1.0 V (with input levels GND or V_{CC}).

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions. Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	
V _{IH}	HIGH-level input voltage	V _{CC} = 1.2 V	0.9	-	-	0.9	-	V
		V _{CC} = 2.0 V	1.4	-	-	1.4	-	V
		V _{CC} = 2.7 V to 3.6 V	2.0	-	-	2.0	-	V
		V _{CC} = 4.5 V to 5.5 V	0.7V _{CC}	-	-	0.7V _{CC}	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 1.2 V	-	-	0.3	-	0.3	V
		V _{CC} = 2.0 V	-	-	0.6	-	0.6	V
		V _{CC} = 2.7 V to 3.6 V	-	-	0.8	-	0.8	V
		V _{CC} = 4.5 V to 5.5 V	-	-	0.3V _{CC}	-	0.3V _{CC}	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}						
		I _O = -100 μA; V _{CC} = 1.2 V	-	1.2	-	-	-	V
		I _O = -100 μA; V _{CC} = 2.0 V	1.8	2.0	-	1.8	-	V
		I _O = -100 μA; V _{CC} = 2.7 V	2.5	2.7	-	2.5	-	V
		I _O = -100 μA; V _{CC} = 3.0 V	2.8	3.0	-	2.8	-	V
		I _O = -100 μA; V _{CC} = 4.5 V	4.3	4.5	-	4.3	-	V
		I _O = -8 mA; V _{CC} = 3.0 V	2.4	2.82	-	2.2	-	V
		I _O = -16 mA; V _{CC} = 4.5 V	3.6	4.2	-	3.5	-	V

Table 6. Static characteristics ...continued

At recommended operating conditions. Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	–40 °C to +85 °C			–40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}						
		I _O = 100 µA; V _{CC} = 1.2 V	-	0	-	-	-	V
		I _O = 100 µA; V _{CC} = 2.0 V	-	0	0.2	-	0.2	V
		I _O = 100 µA; V _{CC} = 2.7 V	-	0	0.2	-	0.2	V
		I _O = 100 µA; V _{CC} = 3.0 V	-	0	0.2	-	0.2	V
		I _O = 100 µA; V _{CC} = 4.5 V	-	0	0.2	-	0.2	V
		I _O = 8 mA; V _{CC} = 3.0 V	-	0.25	0.40	-	0.50	V
		I _O = 16 mA; V _{CC} = 4.5 V	-	0.35	0.55	-	0.65	V
I _I	input leakage current	V _I = V _{CC} or GND; V _{CC} = 5.5 V	-	-	1.0	-	1.0	µA
I _{OZ}	OFF-state output current	V _I = V _{IH} or V _{IL} ; V _O = V _{CC} or GND; V _{CC} = 5.5 V	-	-	5	-	10	µA
I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 5.5 V	-	-	20	-	160	µA
ΔI _{CC}	additional supply current	per input; V _I = V _{CC} – 0.6 V; V _{CC} = 2.7 V to 3.6 V	-	-	500	-	850	µA
C _I	input capacitance		-	3.5	-	-	-	pF

[1] Typical values are measured at T_{amb} = 25 °C.

10. Dynamic characteristics

Table 7. Dynamic characteristicsVoltages are referenced to GND (ground = 0 V). For test circuit see [Figure 10](#).

Symbol	Parameter	Conditions	–40 °C to +85 °C			–40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	
t _{pd}	propagation delay	CP to Qn; see Figure 7 ^[2]						
		V _{CC} = 1.2 V	-	80	-	-	-	ns
		V _{CC} = 2.0 V	-	27	34	-	43	ns
		V _{CC} = 2.7 V	-	20	25	-	31	ns
		V _{CC} = 3.0 V to 3.6 V; C _L = 15 pF ^[3]	-	13	-	-	-	ns
		V _{CC} = 3.0 V to 3.6 V ^[3]	-	15	20	-	25	ns
		V _{CC} = 4.5 V to 5.5 V	-	-	17	-	21	ns
t _{en}	enable time	OE to Qn; see Figure 8 ^[4]						
		V _{CC} = 1.2 V	-	70	-	-	-	ns
		V _{CC} = 2.0 V	-	24	34	-	43	ns
		V _{CC} = 2.7 V	-	18	25	-	31	ns
		V _{CC} = 3.0 V to 3.6 V ^[3]	-	13	20	-	25	ns
		V _{CC} = 4.5 V to 5.5 V	-	-	17	-	21	ns

Table 7. Dynamic characteristics ...continuedVoltages are referenced to GND (ground = 0 V). For test circuit see [Figure 10](#).

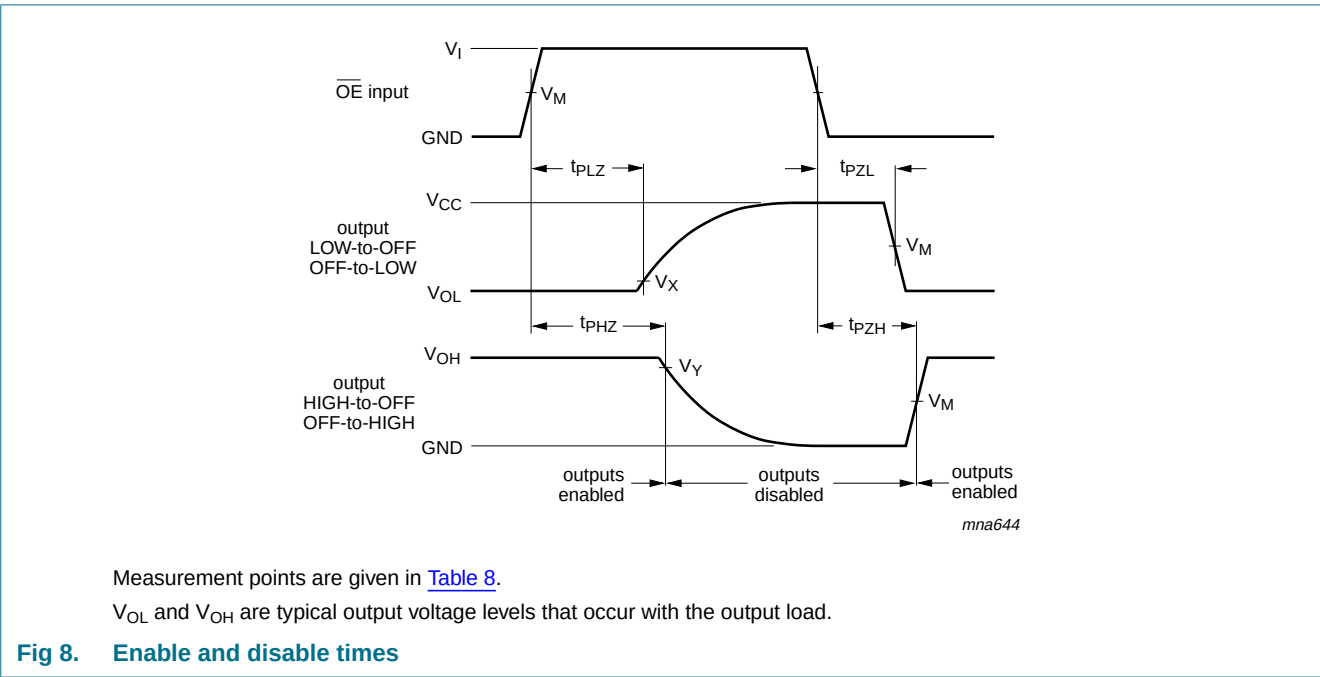
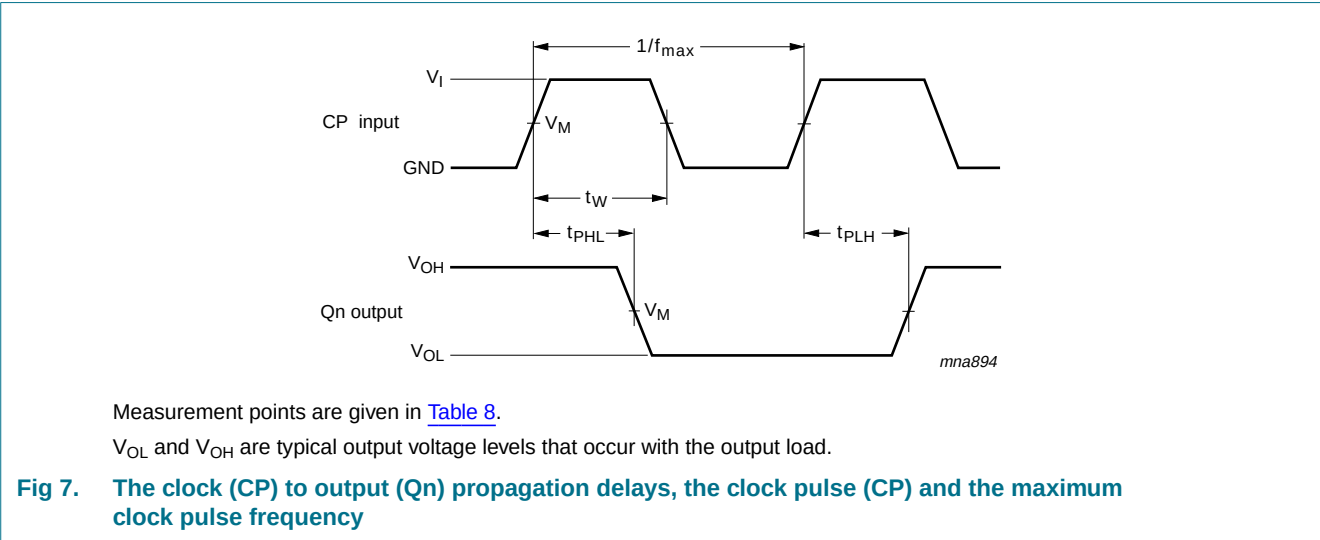
Symbol	Parameter	Conditions	–40 °C to +85 °C			–40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	
t _{dis}	disable time	OE to Qn; Figure 8						
		V _{CC} = 1.2 V	-	75	-	-	-	ns
		V _{CC} = 2.0 V	-	27	27	-	34	ns
		V _{CC} = 2.7 V	-	21	21	-	26	ns
		V _{CC} = 3.0 V to 3.6 V	[3]	16	17	-	21	ns
		V _{CC} = 4.5 V to 5.5 V	[3]	-	15	-	18	ns
t _w	pulse width	CP, HIGH or LOW; see Figure 7						
		V _{CC} = 2.0 V	34	9	-	41	-	ns
		V _{CC} = 2.7 V	25	6	-	30	-	ns
		V _{CC} = 3.0 V to 3.6 V	[3]	20	5	-	24	-
t _{su}	set-up time	Dn to CP; see Figure 9						
		V _{CC} = 1.2 V	-	10	-	-	-	ns
		V _{CC} = 2.0 V	22	4	-	26	-	ns
		V _{CC} = 2.7 V	16	3	-	19	-	ns
		V _{CC} = 3.0 V to 3.6 V	[3]	13	2	-	15	-
t _h	hold time	Dn to CP; see Figure 9						
		V _{CC} = 1.2 V	-	–10	-	-	-	ns
		V _{CC} = 2.0 V	5	–4	-	5	-	ns
		V _{CC} = 2.7 V	5	–3	-	5	-	ns
		V _{CC} = 3.0 V to 3.6 V	[3]	5	–2	-	5	-
f _{max}	maximum frequency	see Figure 7						
		V _{CC} = 2.0 V	15	40	-	12	-	MHz
		V _{CC} = 2.7 V	19	58	-	16	-	MHz
		V _{CC} = 3.0 V to 3.6 V	[3]	24	70	-	20	-
C _{PD}	power dissipation capacitance	C _L = 50 pF; f _i = 1 MHz; V _I = GND to V _{CC}	[6]	25				pF

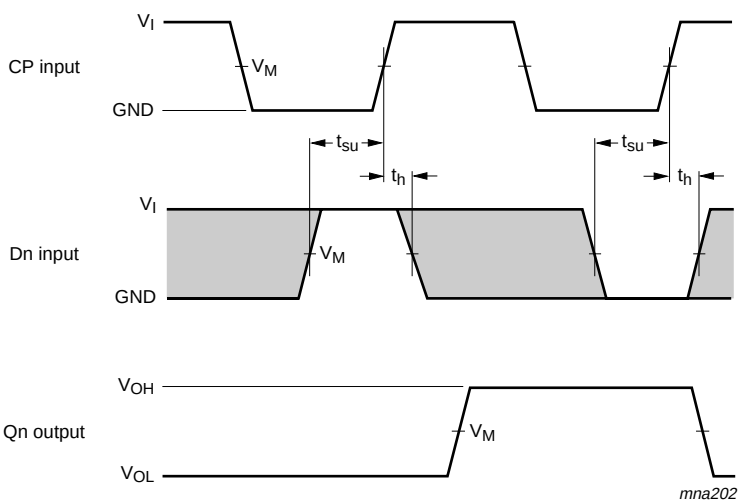
[1] Typical values are measured at T_{amb} = 25 °C.[2] t_{pd} is the same as t_{PLH} and t_{PHL}.[3] Typical value measured at V_{CC} = 3.3 V.[4] t_{en} is the same as t_{PZH} and t_{PZL}.[5] t_{dis} is the same as t_{PHZ} and t_{PLZ}.[6] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).P_D = C_{PD} × V_{CC}² × f_i × N + Σ(C_L × V_{CC}² × f_o) where:f_i = input frequency in MHz;f_o = output frequency in MHz;C_L = output load capacitance in pF;V_{CC} = supply voltage in V;

N = number of inputs switching;

Σ(C_L × V_{CC}² × f_o) = sum of outputs.

11. Waveforms



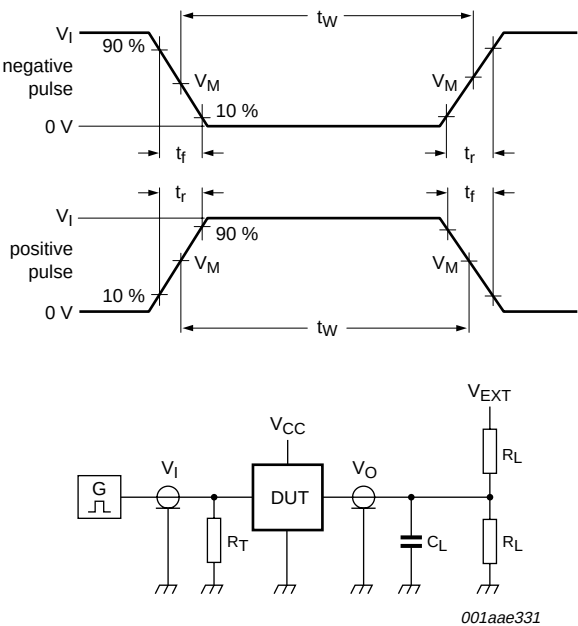


Measurement points are given in [Table 8](#).
The shaded areas indicate when the input is permitted to change for predictable output performance.
 V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 9. The data set-up and hold times for the Dn input to the CP input)

Table 8. Measurement points

Supply voltage V_{CC}	Input	Output		
	V_M	V_M	V_x	V_y
< 2.7 V	$0.5V_{CC}$	$0.5V_{CC}$	$V_{OL} + 0.3\text{ V}$	$V_{OH} - 0.3\text{ V}$
2.7 V to 3.6 V	1.5 V	1.5 V	$V_{OL} + 0.3\text{ V}$	$V_{OH} - 0.3\text{ V}$
$\geq 4.5\text{ V}$	$0.5V_{CC}$	$0.5V_{CC}$	$V_{OL} + 0.3\text{ V}$	$V_{OH} - 0.3\text{ V}$



Test data is given in [Table 9](#).
Definitions for test circuit:
 R_L = Load resistance.
 C_L = Load capacitance including jig and probe capacitance.
 R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.
 V_{EXT} = External voltage for measuring switching times.

Fig 10. Test circuit for measuring switching times

Table 9. Test data

Supply voltage	Input		Load		V_{EXT}		
V_{CC}	V_I	t_r, t_f	C_L	R_L	t_{PHL}, t_{PLH}	t_{PZH}, t_{PHZ}	t_{PZL}, t_{PLZ}
< 2.7 V	V_{CC}	≤ 2.5 ns	50 pF	1 k Ω	open	GND	$2V_{CC}$
2.7 V to 3.6 V	2.7 V	≤ 2.5 ns	15 pF, 50 pF	1 k Ω	open	GND	$2V_{CC}$
≥ 4.5 V	V_{CC}	≤ 2.5 ns	50 pF	1 k Ω	open	GND	$2V_{CC}$

12. Package outline

DIP20: plastic dual in-line package; 20 leads (300 mil)

SOT146-1

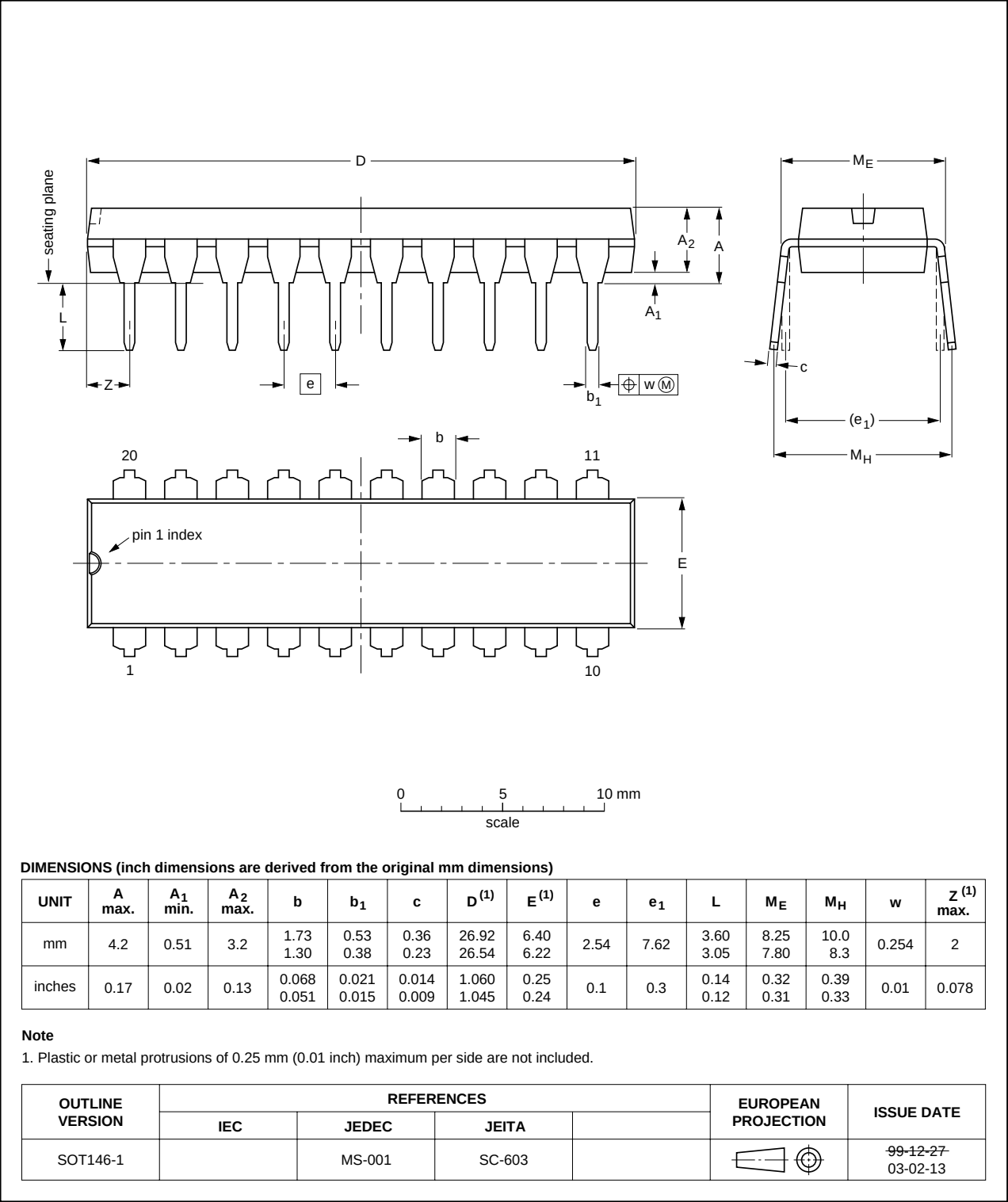


Fig 11. Package outline SOT146-1 (DIP20)

SO20: plastic small outline package; 20 leads; body width 7.5 mm

SOT163-1

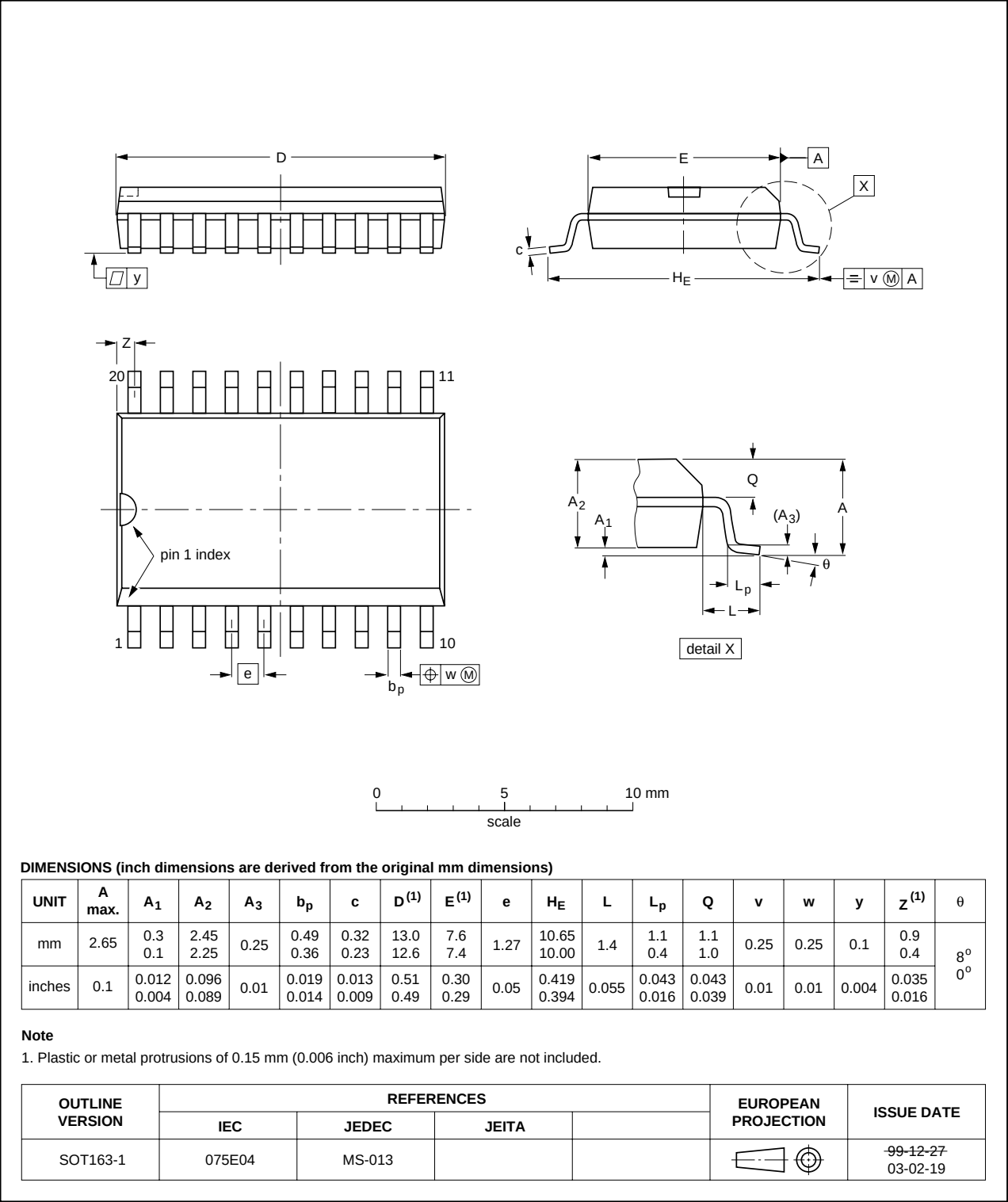


Fig 12. Package outline SOT163-1 (SO20)

SSOP20: plastic shrink small outline package; 20 leads; body width 5.3 mm

SOT339-1

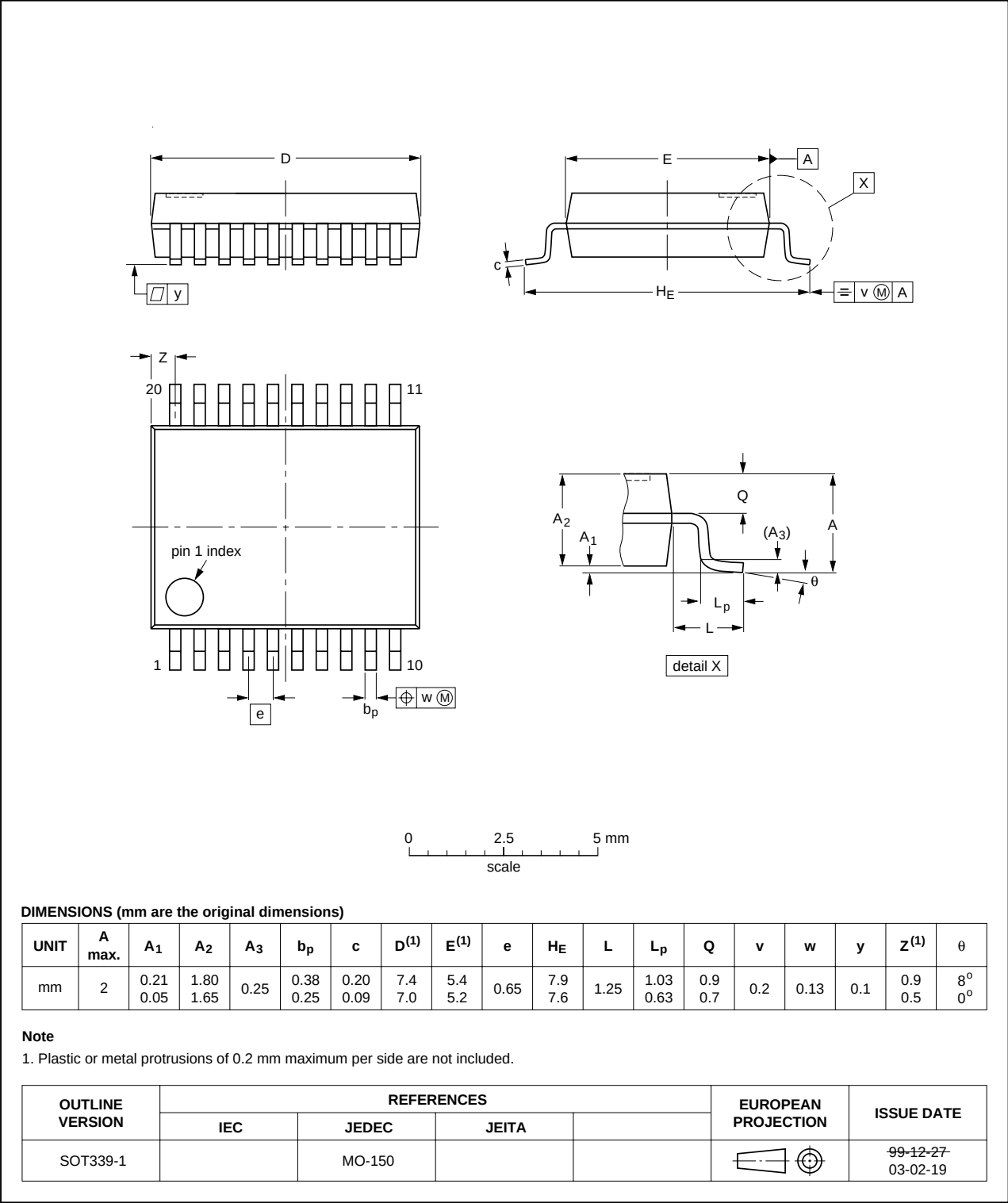


Fig 13. Package outline SOT339-1 (SSOP20)

TSSOP20: plastic thin shrink small outline package; 20 leads; body width 4.4 mm

SOT360-1

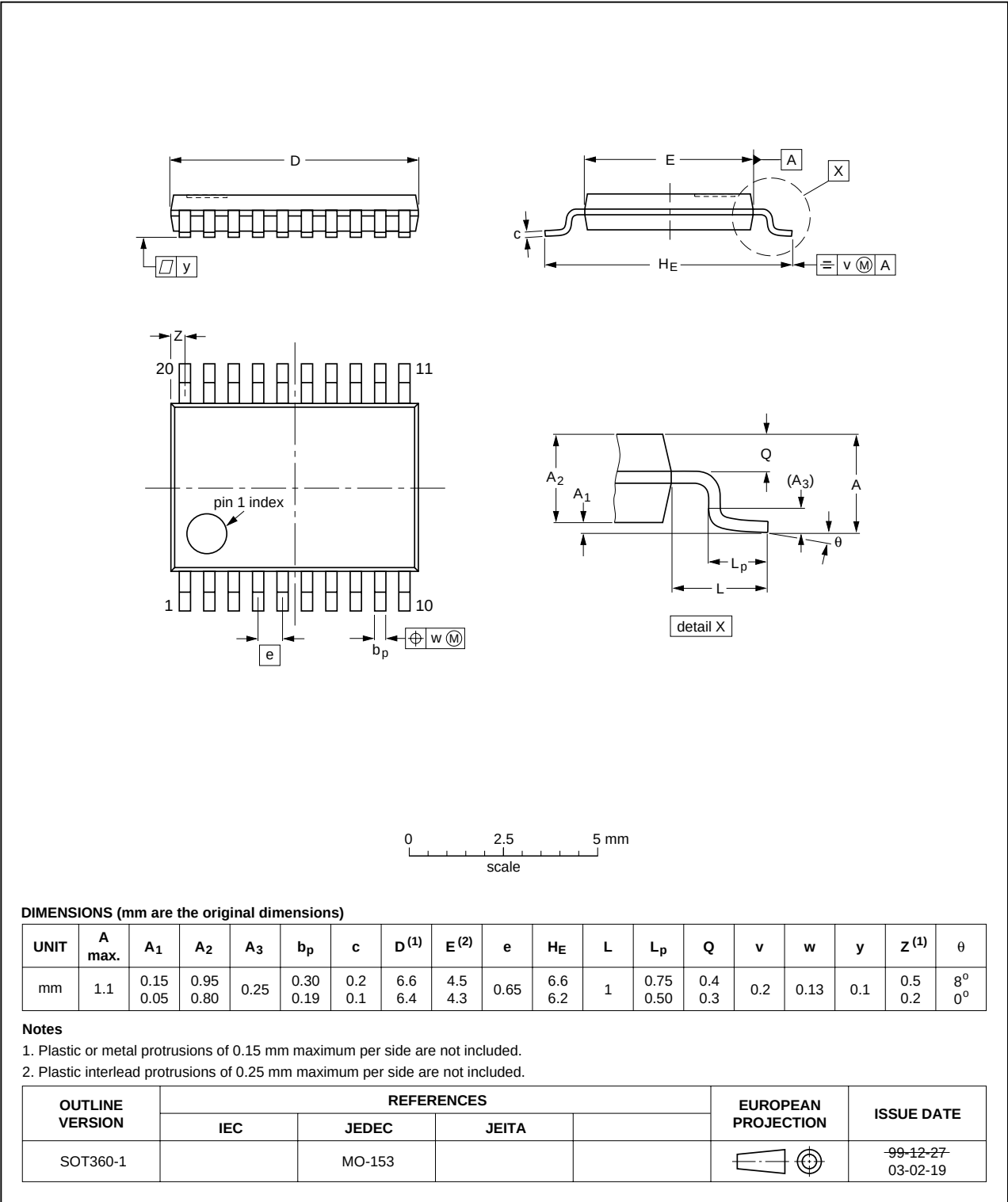


Fig 14. Package outline SOT360-1 (TSSOP20)

13. Abbreviations

Table 10. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

14. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74LV574_4	20090514	Product data sheet	-	74LV574_3
Modifications:	• Typo removed from Figure 8 and Table 8 adapted accordingly			
74LV574_3	20090416	Product data sheet	-	74LV574_2
74LV574_2	19970203	Product specification	-	74LV574_1
74LV574_1	19980610	Product specification	-	-

15. Legal information

15.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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